

## G8550

### PNP EPITAXIAL TRANSISTOR

#### Description

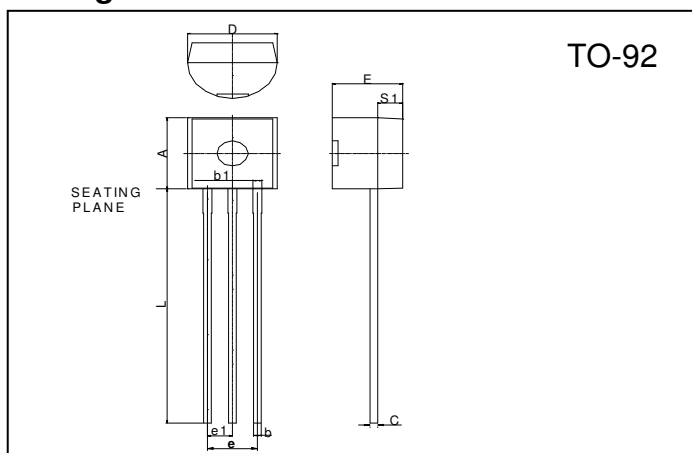
The G8550 is designed for use in 2W output amplifier of portable radios in class B push-pull operation.

#### Features

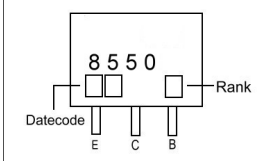
\*High Collector current (IC: 1.5A)

\*Complementary to G8050

#### Package Dimensions



#### Marking :



| REF. | Millimeter |      | REF. | Millimeter |       |
|------|------------|------|------|------------|-------|
|      | Min.       | Max. |      | Min.       | Max.  |
| A    | 4.45       | 4.7  | D    | 4.44       | 4.7   |
| S1   | 1.02       | -    | E    | 3.30       | 3.81  |
| b    | 0.36       | 0.51 | L    | 12.70      | -     |
| b1   | 0.36       | 0.76 | e1   | 1.150      | 1.390 |
| C    | 0.36       | 0.51 | e    | 2.42       | 2.66  |

#### Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

| Parameter                    | Symbol | Ratings    | Unit |
|------------------------------|--------|------------|------|
| Collector to Base Voltage    | VCBO   | -40        | V    |
| Collector to Emitter Voltage | VCEO   | -25        | V    |
| Emitter to Base Voltage      | VEBO   | -6         | V    |
| Collect Current              | IC     | -1.5       | A    |
| Base Current                 | IB     | -0.5       | A    |
| Junction Temperature         | Tj     | +150       | °C   |
| Storage Temperature Range    | TSTG   | -55 ~ +150 | °C   |
| Total Power Dissipation      | Pd     | 1          | W    |

#### Electrical Characteristics (Ta = 25°C, unless otherwise specified)

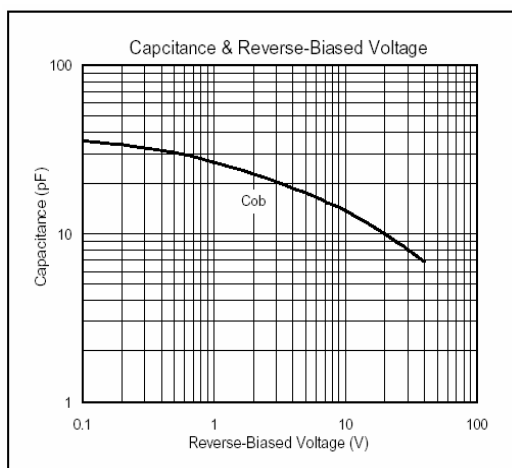
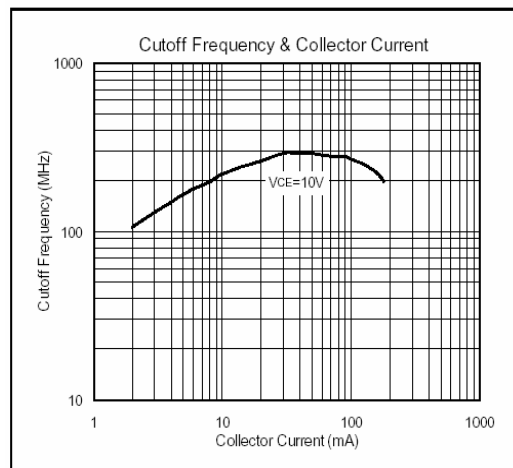
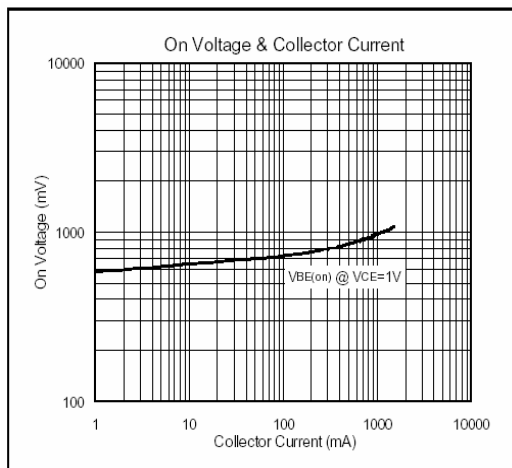
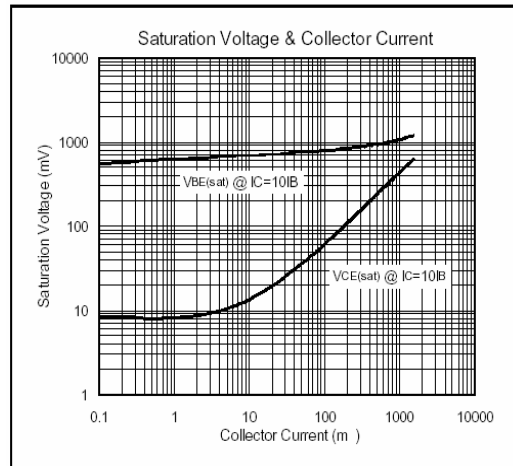
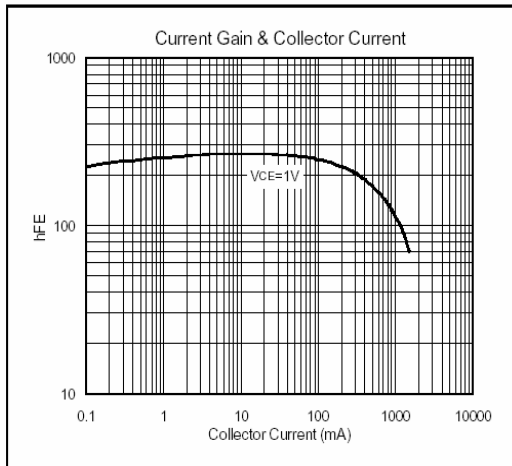
| Symbol    | Min. | Typ. | Max. | Unit | Test Conditions              |
|-----------|------|------|------|------|------------------------------|
| BVCBO     | -40  | -    | -    | V    | IC=-100uA                    |
| BVCEO     | -25  | -    | -    | V    | IC=-2mA                      |
| BVEBO     | -6   | -    | -    | V    | IE=-100uA                    |
| ICBO      | -    | -    | -100 | nA   | VCB=-35V                     |
| IEBO      | -    | -    | -100 | nA   | VBE=-6V                      |
| *VCE(sat) | -    | -    | -0.5 | V    | IC=-800mA, IB=-80mA          |
| *VBE(sat) | -    | -    | -1.2 | V    | IC=-800mA, IB=-80mA          |
| *VBE(on)  | -    | -    | -1   | V    | VCE=-1V, IC=-10mA            |
| *hFE1     | 45   | -    | -    |      | VCE=-1V, IC=-5mA             |
| *hFE2     | 120  | -    | 500  |      | VCE=-1V, IC=-100mA           |
| *hFE3     | 40   | -    | -    |      | VCE=-1V, IC=-800mA           |
| fT        | 100  | -    | -    | MHz  | VCE=-10V, IC=-50mA, f=100MHz |
| Cob       | -    | 9    | -    | pF   | VCB=-10V, IE=0, f=1MHz       |

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE2

| Rank  | C         | D         | E         |
|-------|-----------|-----------|-----------|
| Range | 120 ~ 200 | 160 ~ 320 | 250 ~ 500 |

## Characteristics Curve



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